

# Citations for Ion = **Li** , Target = **Si**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1970</b>	Apel, D. Muller-Jahreis, U. Schwabe, S. <b>'On the Z2-Dependence of Electronic Stopping Cross Section'</b> <i>Phys. Stat. Sol. A, 3, K173-75 (1970)</i> <i>Comment : S. 10-100 keV Li -&gt; Si, V, Cr, Fe, Ge, Se</i>	<b>1970-Apel</b> 0655
<b>1974</b>	Baranova, E. K. Gusev, V. M. Streletsov, L. N. <b>'Distribution of Defects with Depth in Silicon Irradiated with 80 keV Lithium Ions'</b> <i>Sov. Phys. Semicond., 7, 1239-1240 (1974)</i> <i>Comment : dR. 80 keV Li -&gt; Si</i>	<b>1974-Bara</b> 0987
<b>1974</b>	Bayadilov, E. M. Vavilov, V. S. Katsaurov, L. N. Krasnopevtsev, V. V. Milyutin, Y. V. <b>'Heat Treatment-Induced Redistribution of the Concentration of Implanted Li Ions in Silicon'</b> <i>Sov. Phys. Semicond., 7, 1225-1226 (1974)</i> <i>Comment : R. 40 keV Li -&gt; Si (With Anneal)</i>	<b>1974-Baya</b> 0986
<b>1975</b>	Neuwirth, W. Pietsch, W. Richter, K. Hauser, U. <b>'Electronic Stopping Cross Sections of Elements and Compounds for Swift Lithium Ions'</b> <i>Z. Physik A, 275, 209-14 (1975)</i> <i>Comment : S. 80-840 keV Li -&gt; Be, B, Al, Ti, Cu, Ta, AlB2, AlB12, B4C, B2O3, BPO4, B4Si, CaB6, CeB6, Crb, Crb2, Cr2B3, H2O, D2O, HBO2, H3BO3, HFB2, KBF4, KBH4, LaB6, LiBH</i>	<b>1975-Neuw2</b> 0813
<b>1975</b>	Skakun, N. A. Grigorev, A. N. Dikii, N. P. Matyash, P. P. Nikolaichuk, L. I. <b>'Investigation into the Profile of Radiation Damage in Si using the Elastic Scattering of 4He Ions'</b> <i>Pis'Ma Zh. Tekh. Fiz. (USSR) 1, 203-7 (1975)</i> <i>Comment : R, dR. 80 keV Li -&gt; Si</i>	<b>1975-Skak2</b> 1264
<b>1976</b>	Emmooth, B. Braun, M. Palenius, H. P. <b>'Implantation Profiles and Sputtering Studied by Detecting the Optical Radiation from Sputtered Particles During Bombardment'</b> <i>J. Nucl. Mater., 63, 482-486 (1976)</i> <i>Comment : R, dR. 10 keV Li -&gt; Ag, V, 20 keV Li -&gt; Si, 20-40 keV Li -&gt; Al, 40 keV Ar -&gt; Ag</i>	<b>1976-Emmo</b> 1070
<b>1976</b>	Hoffman, I. Jager, E. Muller-Jahreis, U. <b>'Z1-Dependence of Electronic Energy Straggling of Light Ions'</b> <i>Rad. Effects, 31, 57 (1976)</i> <i>Comment : dS. 2 &lt;= Z1 &lt;= 10 (10-100 Kev) -&gt; C, Si</i>	<b>1976-Hoff</b> 1259
<b>1976</b>	Kovaleva, E. A. Korol, V. M. Merrik, B. R. <b>'Ranges of Metals in Amorphous Si and Ge'</b> <i>Elektronnaya Texnika, 2, 33-38 (1976)</i> <i>Comment : R, dR. 10-200 keV Li, Na, K, Rb, Cs -&gt; Si, Ge, Al, Ni</i>	<b>1976-Kova</b> 0944

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<b>1976</b>	Neuwirth, W. Pietsch, W. Hauser, U. <b>'Stopping Cross Sections of Elements with Z=2 to 87 for Li Ions with Energies Between 80 keV and 840 keV'</b> <i>Physics Data, Erstes Phsikalisches Institut, Univ. Zu Kln, Germany (1976)</i> Comment : S. 80-840 keV Li -> (2 <= Z2 <= 87)	<b>1976-Neuw</b> 1178
<b>1977</b>	Thompson, D. A. Robinson, J. E. Walker, R. S. <b>'Inelastic Stopping of Medium Energy Light Ions in Silicon'</b> <i>Rad. Effects, 32, 169-175 (1977)</i> Comment : dS,R,dR. 10-80 keV H, He, Li, B, C, N, O, Ne -> Si	<b>1977-Thom</b> 1076
<b>1979</b>	Comas, J. Wilson, R. G. <b>'Channeling and Random Equivalent Depth Distributions of 150 keV Li, Be, and B Implanted in Si'</b> <i>Preprint (1979) 2</i> Comment : S, R, dR. 150 keV Li, Be, B -> Si	<b>1979-Coma</b> 1145
<b>1980</b>	Sofield, C. J. Cowern, N. E. B. Freeman, J. M. <b>'Charge-Exchange Effects in Energy-Loss Straggling'</b> <i>Nucl. Inst. Methods, 170, 221-225 (1980)</i> Comment : R, dR. 0-50 MeV Atomic Numbers 1-16 -> Al	<b>1980-Sofi</b> 1378
<b>1983</b>	Wach, W. Wittmaack, K. <b>'Ranges of Low Energy Light Ions in Amorphous Silicon'</b> <i>Phys. Rev. B, 27 (6), 3528-3537 (1983)</i> Comment : R, dR. Li, B, N, O, F, Na, Mg, Al ((1-20 keV) -> Si	<b>1983-Wach</b> 1528
<b>1984</b>	Santry, D. C. Werner, R. D. <b>'Stopping Powers of C, Al, Si, Ti, Ni, Ag and Au for Li-7 Ions'</b> <i>Nucl. Inst. Methods, B5, 449 (1984)</i> Comment : S. Li (0.2-1.8 MeV) -> C, Al, Si, Ni, Ag, Au	<b>1984-Sant2</b> 1758
<b>1989</b>	Behar, M. Weiser, M. Kalbitzer, S. Fink, D. Grande, P. L. <b>'High Energy Li Implanted Profiles in Silicon'</b> <i>Nucl. Inst. Methods, B39, 22-25 (1989)</i> Comment : R, dR. Li (4.5keV-2 MeV) -> Si	<b>1989-Beha</b> 1516
<b>1991</b>	Kuronen, A. <b>'A Study of Stopping Power using Nuclear Methods'</b> <i>Comm. Physico-Math. (Finland), 122, 1-36 (1991)</i> Comment : S. Ion [Z=3-22] at (0-0.4 Vo) -> Solids (Z=14-82)	<b>1991-Kuro</b> 1914
<b>1995</b>	Li, Z. Zhou, Z. Y. Zhao, G. Q. Tang, J. Y. Yang, F. <b>'Measured Stopping Powers for Li Ions in Silicon Single Crystal at 1-5 MeV'</b> <i>Chinese Phys. Letters, 13, 172-174 (1995)</i> Comment : S. Li (1-5 MeV) -> Si	<b>1995-Li</b> 1825

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<b>1996</b>	Gelfort, S. Kerkow, H. Stolle, R. Petukhov, V. P. Romanowski, E. A. 'Angular Dependence of the Electronic Energy Loss for Low Energy Heavy Ions under Channeling Conditions' <i>Nucl. Inst. Methods, B115, 315-318 (1996)</i> <i>Comment : S. Channeling of ions He to Kr in Si &lt;110&gt;</i>	<b>1996-Gelf</b> 1814
<b>1996</b>	Li, Z. Zhao, G. Q. Zhou, Z. Y. Tang, J. Y. Yang, F. C. 'Measured Stopping Powers of Li Ions in Silicon Single Crystal at 1-5 MeV' <i>Chinese Phys. Letters, 13, 172-174 (1996)</i> <i>Comment : S. Li (1.0 - 5.0 MeV) -&gt; Si (channeling effects)</i>	<b>1996-Li</b> 2064
<b>1996</b>	Liu, J. R. Zheng, Z. S. Chu, W. K. 'Stopping Cross Sections of C, Al, Si for Li-7 Ions' <i>Nucl. Inst. Methods, 118, 24-28 (1996)</i> <i>Comment : S. Li (1-7 MeV) -&gt; C, Al, Si</i>	<b>1996-Liu</b> 0592
<b>1996</b>	Misdaq, M. A. Elassali, R. 'Average Stopping Powers for Channeled Ions using Calculational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -&gt; Si, GaAs (channeled)</i>	<b>1996-Misd</b> 0964
<b>1999</b>	Jiang, W. Grotzschel, W. Pilz, W. Schmidt, B. Moller, W. 'Random and Channeling Stopping Powers and Charge State Distributions in Silicon for 0.2 - 1.2 MeV/u Positive Heavy Ions' <i>Phys. Rev. B, 59, 226-234 (1999)</i> <i>Comment : S. Li, B, C, N, O, P, Cl (0.2 - 1.2 MeV/u) -&gt; Si</i>	<b>1999-Jian</b> 2333
<b>2000</b>	DaSilva, D. L. Azevedo, G. de M. Behar, M. Dias, J. F. Grande, P. L. 'Random Energy Loss and Straggling Study of Li into Si' <i>Nucl. Inst. Methods, B175-177, 98-101 (2001)</i> <i>Comment : S. dS. Li (380 - 2500 keV) -&gt; Si</i>	<b>2000-daSi</b> 2348